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U.S. UTILITY Patent Application

PATENT NUMBER and
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10083991	02/26/2002	438	424	2812	ISAC

**APPLICANTS: Chang Chia-Der; Yen Yi-Tung;

**CONTINUING DATA VERIFIED:

** FOREIGN APPLICATIONS VERIFIED:

PG-PUB DO NOT PUBLISH <input checked="" type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input type="checkbox"/> yes <input checked="" type="checkbox"/> no	ATTORNEY DOCKET NO
35 USC 119 conditions met <input type="checkbox"/> yes <input checked="" type="checkbox"/> no	TS01-660
Verified and Acknowledged Examiners's initials <i>Harvella Law SDT</i>	
TITLE : Planarization method for deep sub micron shallow trench isolation process	
U.S. DEPT. OF COMM./PAT. & TM-PTO-436L (Rev. 12-94)	

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
Assistant Examiner		DRAWING	
		Sheets Drwg.	Figs. Drwg.
Primary Examiner		Print Fig.	
Application Examiner			
PREPARED FOR ISSUE			
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DISCLAIMER			

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